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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Complete if Known

Application Number	10/535,358
Filing Date	
First Named Inventor	Andrew R. Barron
Group Art Unit	
Examiner Name	
Attorney Docket Number	1789-09405 (21050) CWS

Sheet	1	of	1
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U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
/TD/	AA	US-6,080,683	06/27/2000		
	AB	US-5,073,408	12/17/1991		
	AC	US-5,132,140	07/21/1992		
	AD	US-5,616,233	04/01/1997		
	AE	US-4,468,420	08/28/1984		
	AF	US-4,693,916	09/15/1987		
	AG	US-4,431,683	02/14/1984		
/TD/	AH	US-2,505,629	04/25/1950		

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ Number + Kind Code ³ (if known)				

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate) title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issued number(s), publisher, city and/or country where published.			T ²
/TD/	AI	"The Initial Growth Mechanism of Silicon Oxide by Liquid-Phase Deposition", Chou, J.-S. and Lee, S.-C., J. Electrochem. Soc., vol. 140, No. 11, Nov. 1994, pp. 3214-3218.			
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	AM	"A New Process for Silica Coating", Nagayama, H., Honda, H., and Kawahara, H., J. Electrochem. Soc.: Solid State Science and Technology, vol. 135, No. 8, Aug. 1988, pp. 2013-2015.			
/TD/	AN	"Characterization of Silica on Surface Preparation Processes for Advanced Gate Dielectrics", Okorn-Schmidt, H. F., IBM J. Res. Develop., vol. 43, No. 3, May 1999, pp. 351-365.			
Examiner Signature	/Trung Dang/			Dated Considered	08/05/2008